

#### RN4905

TOSHIBA Transistor Control of the Solution Silicon PNP Epitaxial Type (PCT Process) Silicon NPN Epitaxial Type (PCT Process)

# **RN4905**

R1: 2.2kΩ

R2: 47kΩ

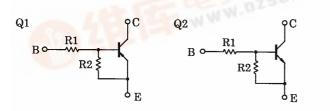
(Q1, Q2 Common)

#### Switching, Inverter Circuit, Interface Circuit And Driver Circuit Applications

• Includeing two devices in US6 (ultra super mini type with 6 leads)

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process

#### **Equivalent Circuit and Bias Resister Values**

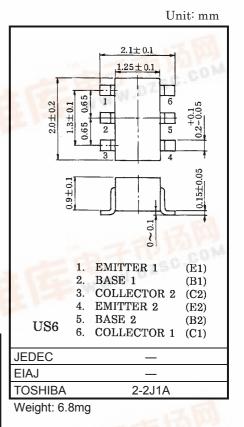


#### Q1 Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V <sub>CBO</sub>	-50	V
Collector-emitter voltage	V <sub>CEO</sub>	-50	V
Emitter-base voltage	V <sub>EBO</sub>	-5	V
Collector current	Ι <sub>C</sub>	-100	mA

#### Q2 Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V <sub>CBO</sub>	50	V
Collector-emitter voltage	V <sub>CEO</sub>	50	V
Emitter-base voltage	V <sub>EBO</sub>	5	V
Collector current	Ι <sub>C</sub>	100	mA



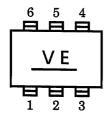
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# Q1, Q2 Common Maximum Ratings (Ta = 25°C)

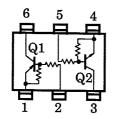
Characteristic	Symbol	Rating	Unit	
Collector power dissipation	P <sub>C</sub> *	200	mW	
Junction temperature	Тj	150	°C	
Storage temperature range	T <sub>stg</sub>	-55~150	°C	

\* : Total rating

### Marking



### Equivalent Circuit (Top View)



# Q1 Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	_	$V_{CB} = -50V, I_E = 0$	-	_	-100	nA
	ICEO	-	V <sub>CE</sub> = -50V, I <sub>B</sub> = 0	_	_	-500	
Emitter cut-off current	I <sub>EBO</sub>		$V_{EB} = -5V, I_C = 0$	-0.078	_	-0.145	mA
DC current gain	h <sub>FE</sub>	-	V <sub>CE</sub> = −5V, I <sub>C</sub> = −10mA	80	_	—	
Collector-emitter saturation voltage	V <sub>CE (sat)</sub>	-	I <sub>C</sub> = −5mA, I <sub>B</sub> = −0.25mA	_	-0.1	-0.3	V
Input voltage (ON)	V <sub>I (ON)</sub>	-	$V_{CE} = -0.2V, I_C = -5mA$	-0.6	_	-1.1	V
Input voltage (OFF)	VI (OFF)		$V_{CE} = -5V, I_C = -0.1mA$	-0.5	_	-0.8	V
Transition frequency	f <sub>T</sub>	_	V <sub>CE</sub> = −10V, I <sub>C</sub> = −5mA	_	200	—	MHz
Collector output capacitance	C <sub>ob</sub>	_	V <sub>CB</sub> = -10V, I <sub>E</sub> = 0	_	3	6	pF

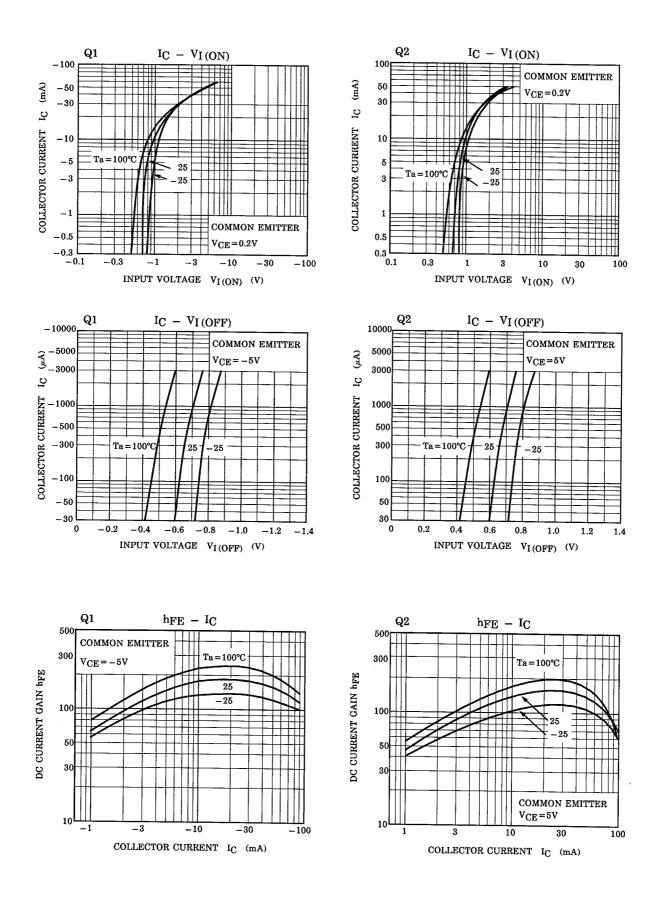
# Q2 Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit	
Collector cut-off current	I <sub>CBO</sub>	-	V <sub>CB</sub> = 50V, I <sub>E</sub> = 0	_	_	100	nA	
	I <sub>CEO</sub>	_	V <sub>CE</sub> = 50V, I <sub>B</sub> = 0	_	_	500	ПА	
Emitter cut-off current	I <sub>EBO</sub>	_	V <sub>EB</sub> = 5V, I <sub>C</sub> = 0	0.078	_	0.145	mA	
DC current gain	h <sub>FE</sub>	_	V <sub>CE</sub> = 5V, I <sub>C</sub> = 10mA	80	_	_	_	
Collector-emitter saturation voltage	V <sub>CE (sat)</sub>	_	I <sub>C</sub> = 5mA, I <sub>B</sub> = 0.25mA	_	0.1	0.3	V	
Input voltage (ON)	V <sub>I (ON)</sub>	_	V <sub>CE</sub> = 0.2V, I <sub>C</sub> = 5mA	0.6	_	1.1	V	
Input voltage (OFF)	V <sub>I (OFF)</sub>	_	V <sub>CE</sub> = 5V, I <sub>C</sub> = 0.1mA	0.5	_	0.8	V	
Transition frequency	fT	—	V <sub>CE</sub> = 10V, I <sub>C</sub> = 5mA	_	250	_	MHz	
Collector output capacitance	C <sub>ob</sub>	—	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f = 1 MHz	_	3	6	pF	

### Q1, Q2 Common Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Input resistor	R1	_	—	1.54	2.2	2.86	kΩ
Resistor ratio	R1/R2	—	_	0.0421	0.0468	0.0515	—

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